



Press Contacts:

Eileen Elam  
KJ Communications (in the U.S.)  
Tel: +1 408 927-7753  
[eileen@kjcompr.com](mailto:eileen@kjcompr.com)

Nick Foot  
Billings PR (in Europe)  
Tel: +44 1491 636393  
[nick.foot@billings-europe.com](mailto:nick.foot@billings-europe.com)

## **Innovative Silicon's Z-RAM® Ultra-Dense Memory Now Backed by 21 Patents**

### **Memory IC Technology Innovator Has 43 Additional Patents Pending**

**SANTA CLARA, Calif., March 27, 2007** — Innovative Silicon (ISi), the developer of Z-RAM® high density memory intellectual property (IP), announced today that it has been awarded its 21st patent and has another 43 more patent applications pending worldwide. For 2007, to date, the company has already been granted four U.S. patents for low power consumption, data storage and other important contributions related to its memory technology. The newest patent numbers include 7,170,807; 7,187,581; 7,184,298 and 7,177,175.

“These patents demonstrate the level of innovation from the exceptional engineering team at ISi that results in a highly differentiated IP offering,” said Mark-Eric Jones, president and CEO of ISi. “We are committed to continue this innovation in order to constantly improve and expand our Z-RAM memory technology and provide our licensees with the compelling solutions that they need for a wide range of different applications.”

ISi's portfolio of patented inventions in the area of ultra-dense semiconductor memory technology that exploits the floating body effect of SOI devices was first presented in 2001 at the IEEE International SOI Conference. Since that time, ISi's Z-RAM technology has unveiled two generations of its products with Z-RAM Gen2 being announced in December 2006. The company has also received tremendous industry recognition and awards. Earlier this year, the company was profiled as one of five winners and the only semiconductor company in *IEEE Spectrum Magazine's* “Winners and Losers 2007” listing. *EE Times* has also named ISi in its list of 60 Emerging Startups - better known as the “Silicon 60” - each year since the list was created in early 2004. Dr. Serguei Okhonin, the company's chief scientist and co-founder, was also named in January as one of the 2007 *EE Times' ACE Award Innovator of the Year* Finalists. Further, ISi was awarded the “Best Invention of the Year” status by the Swiss Federal Institute of Technology (EPFL) in 2002.

### **About Innovative Silicon**

Innovative Silicon Inc. (ISi) delivers ultra-high density memory IP for embedded SoC, MPU and

portable consumer applications requiring low power, high density and high speed. Endorsed by *IEEE Spectrum Magazine* in January 2007 as the 'winning' semiconductor technology, ISI's Z-RAM<sup>®</sup> memory offers up to twice the density of embedded DRAM and is up to five times denser than embedded SRAM. The company closed its first round of VC funding in 2003, completed its first 90nm megabit Z-RAM memory designs in 2004, its first 65nm designs in 2005 and its first 45nm designs in 2006. With more than 20 patents already granted, Z-RAM<sup>®</sup>'s unique single-transistor architecture is the world's lowest cost semiconductor memory solution. The company is incorporated in the USA with R&D in Lausanne, Switzerland. For more information see [www.z-ram.com](http://www.z-ram.com).

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